

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 1 of 2

**Complete if Known**

Application Number	
Filing Date	October 14, 2003
First Named Inventor	Enzo CAROLLO
Art Unit	
Examiner Name	
Attorney Docket Number	2110-81-3

**U.S. PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		EP 1 168 427 A1	01/02/02	Applied Materials, Inc.		
		EP 1 111 664 A2	06/27/01	Applied Materials, Inc.		

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First Named Inventor

Enzo Carollo

Group Art Unit

Examiner Name

Attorney Docket Number

2110-81-3

**OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		J. YOTA, et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications", 0-7803-6327-2/00 2000 IEEE, pp. 76-78	
		J. YOTA, et al., "A Comparative Study on Inductively-coupled Plasma High-density Plasma, Plasma-enhanced, and Low Pressure Chemical Vapor Deposition Silicon Nitride Films", J. Vac. Sci. Technol. A 18(2) Mar/Apr 2000 0734-2101/2000/18(2)/372/5 2000 American Vacuum Society, pp. 372-375	
		S. V. NGUYEN, "High-density Plasma Chemical Vapor Deposition of Silicon-based Dielectric Films for Integrated Circuits", 0018-8646/99 1999 IBM, 21 pages	
		European Search Report for EP 02 42 5615 dated May 7, 2003	

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